

APPROVED	O.G. FIG.	
BY	CLASS	SUBCLASS
DRAFTSMAN		

Title: Gallium-Nitride Semiconductor . . . Source Device.
 Inventor: Toshiyuki OKUMURA
 Application No.: NEW
 Docket No.: 204552016410

Fig.1

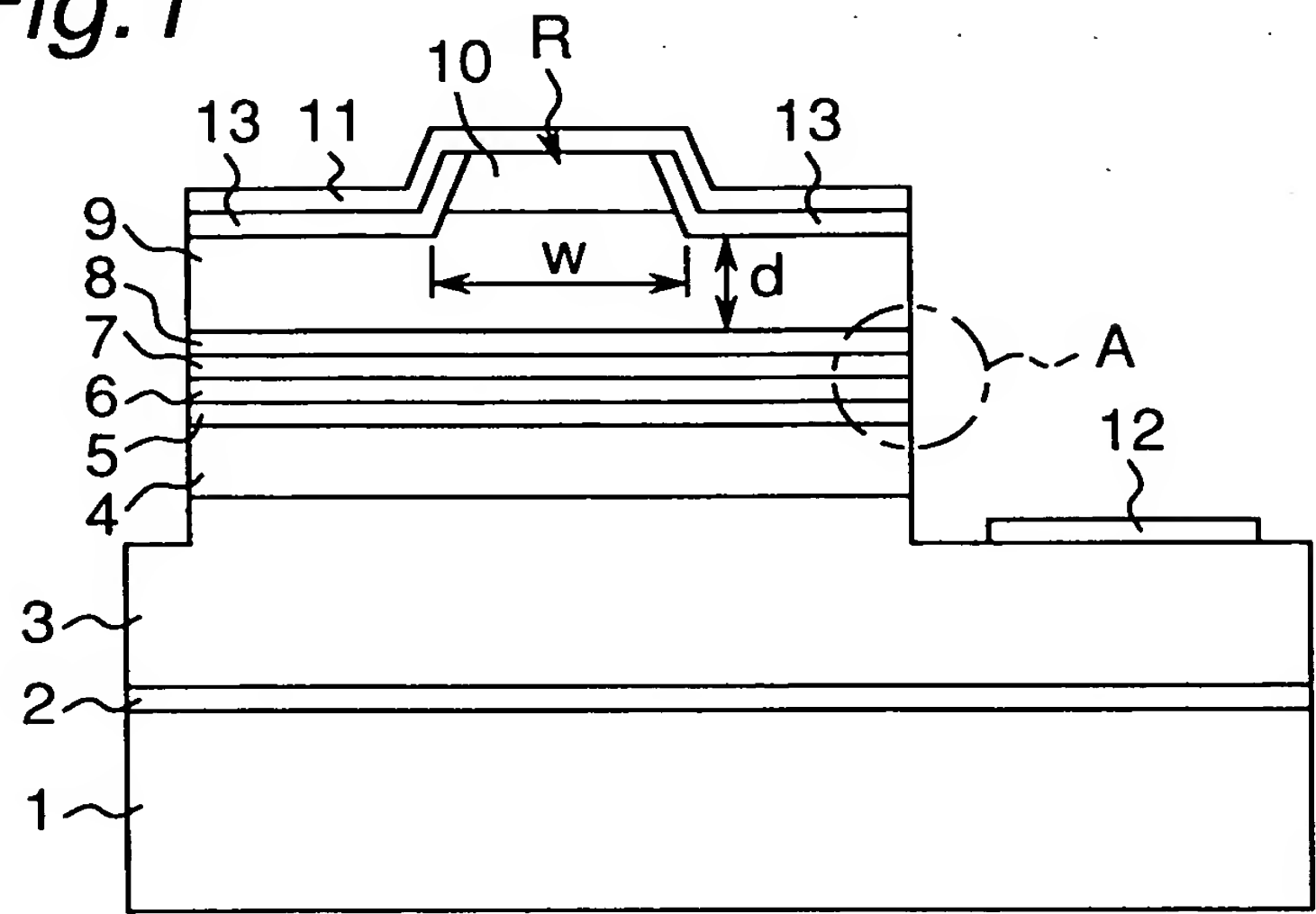


Fig.2

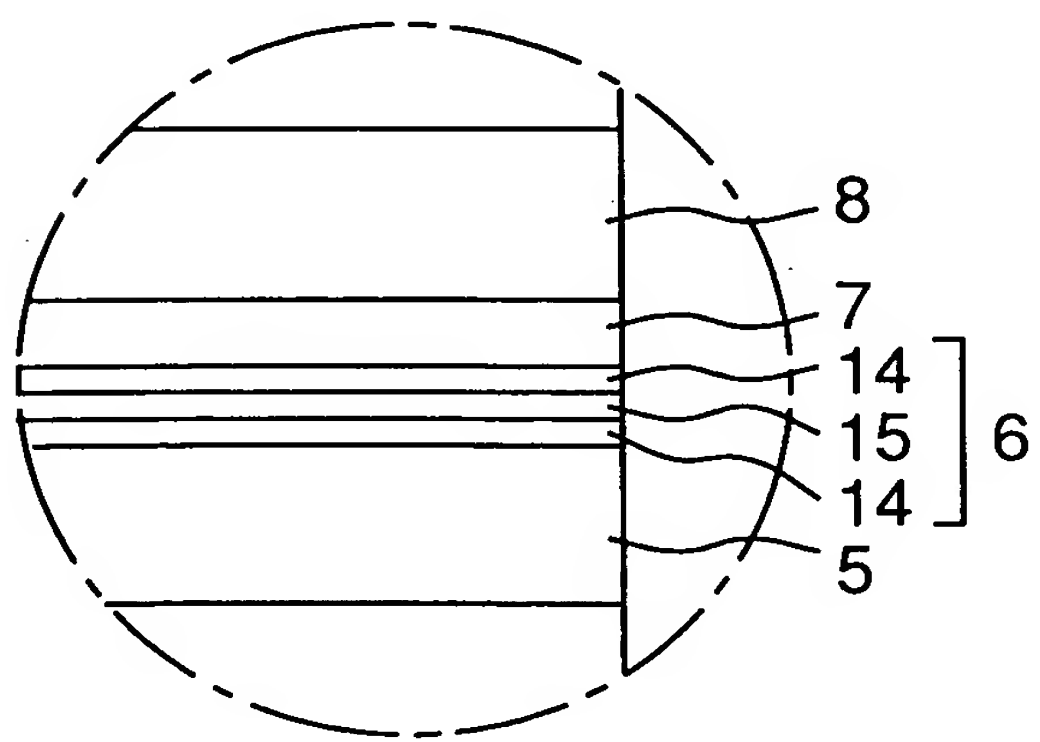


Fig.3

Frequency Capable of Modulating
Optical Output power
(Max. Frequency=●)

Threshold Current (○)

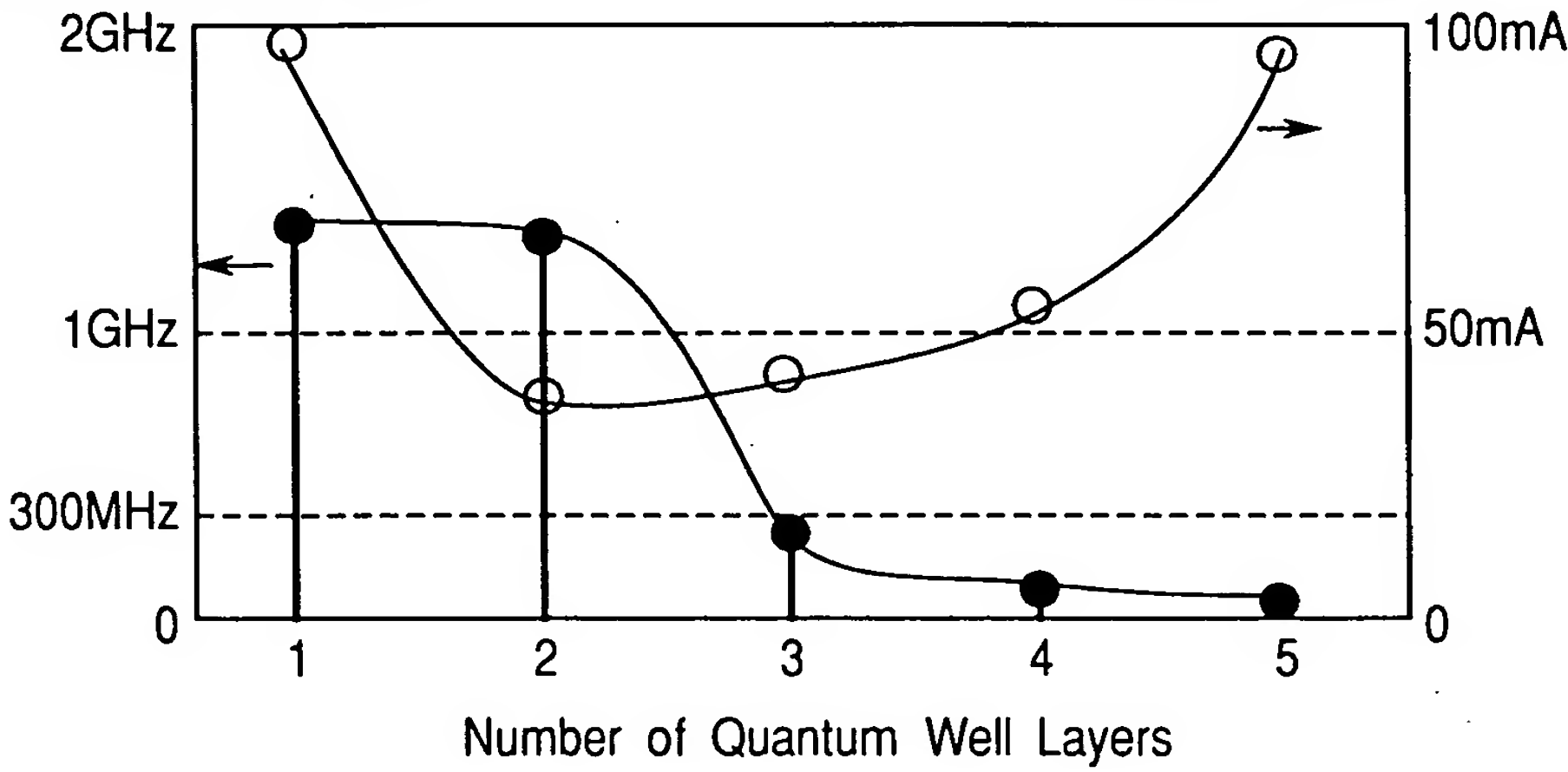
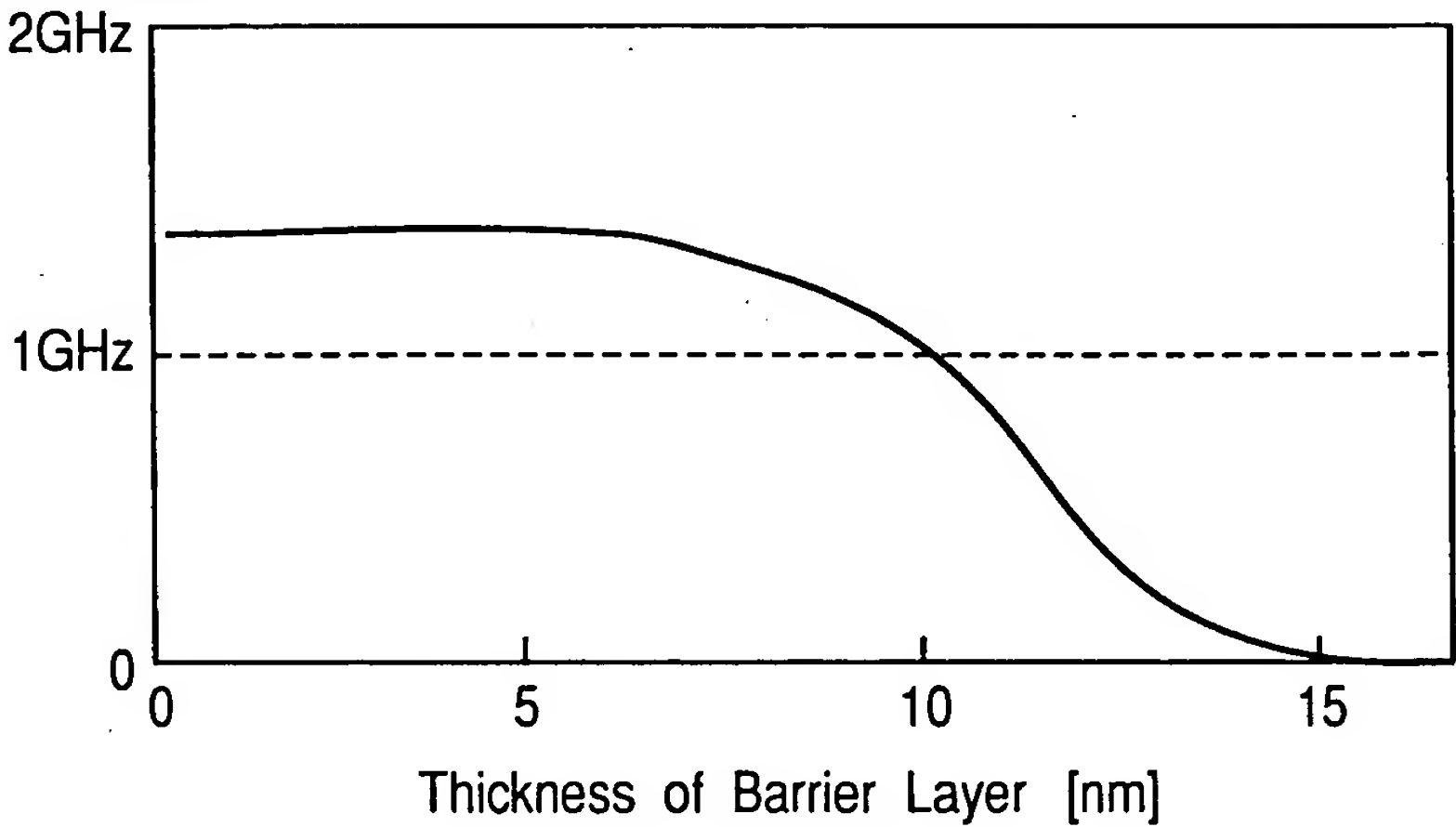


Fig.4

Frequency Capable of Modulating
Optical Output power



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Fig.5

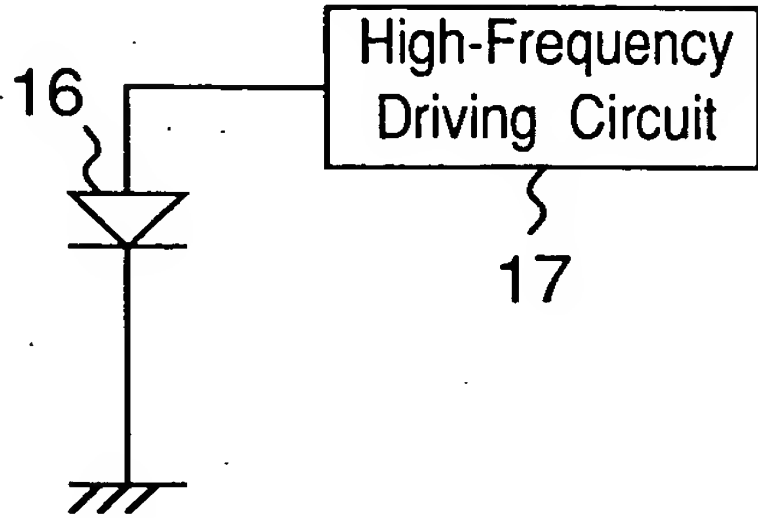


Fig.6

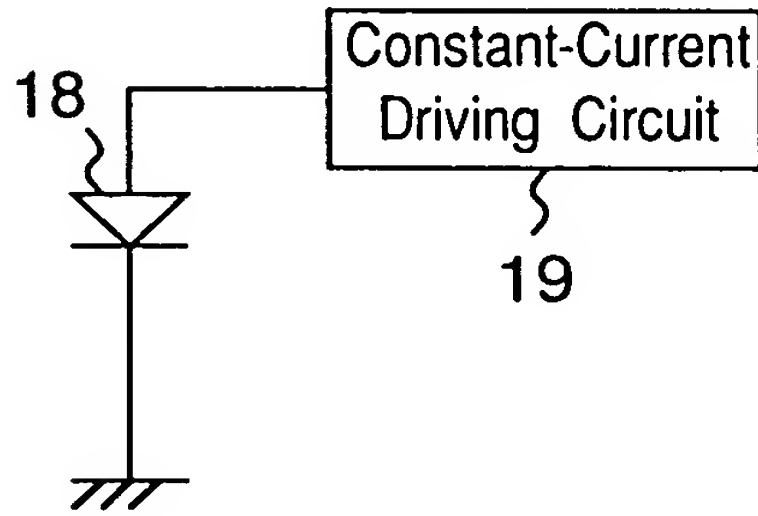


Fig.7

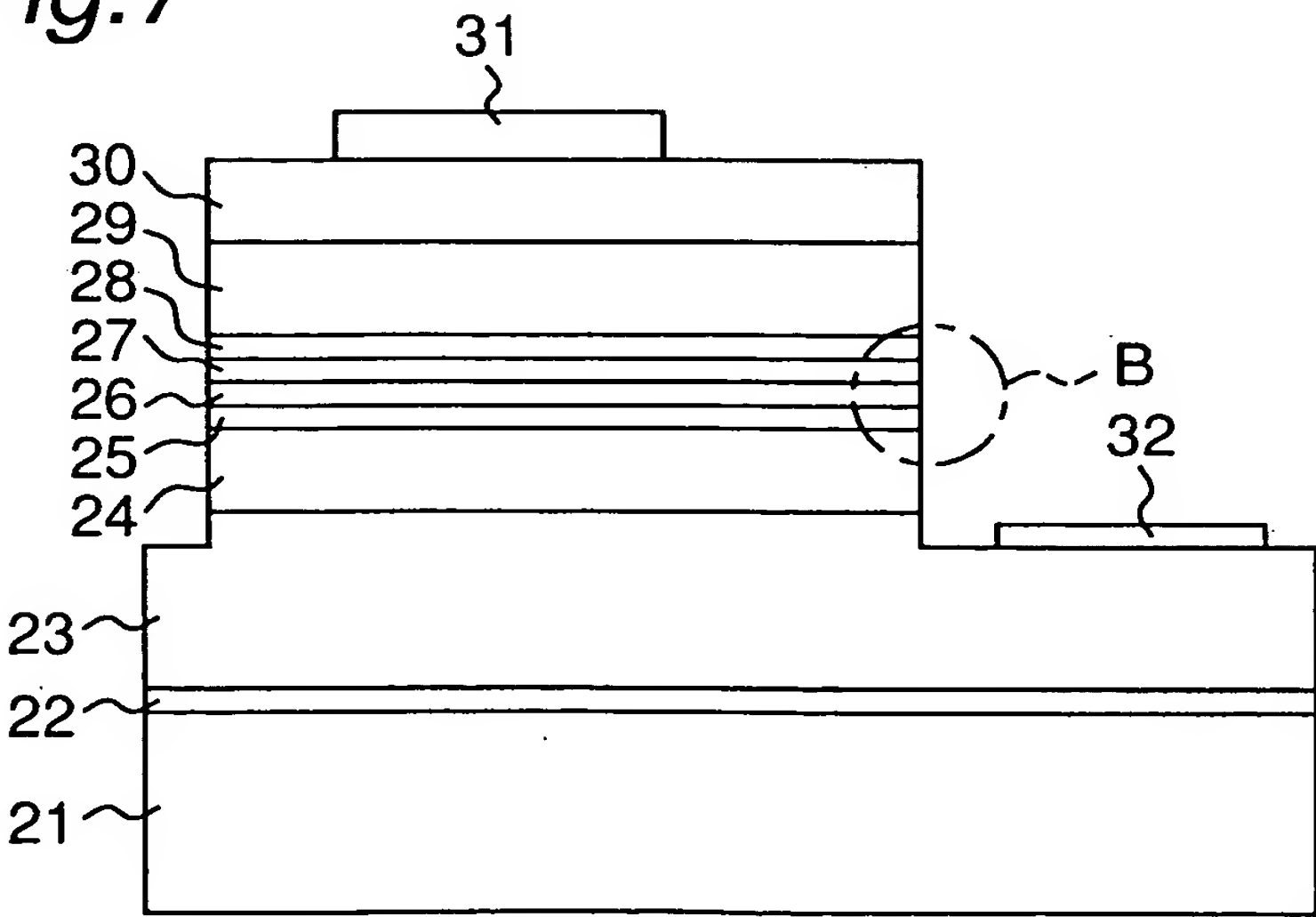


Fig.8

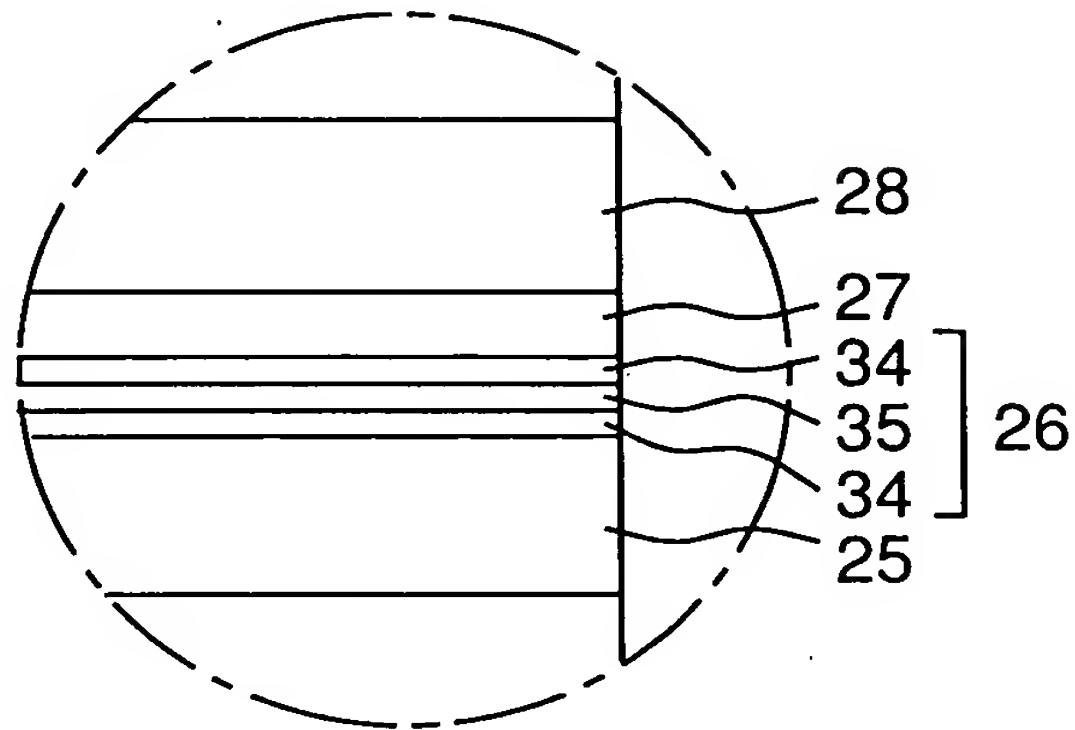


Fig.9

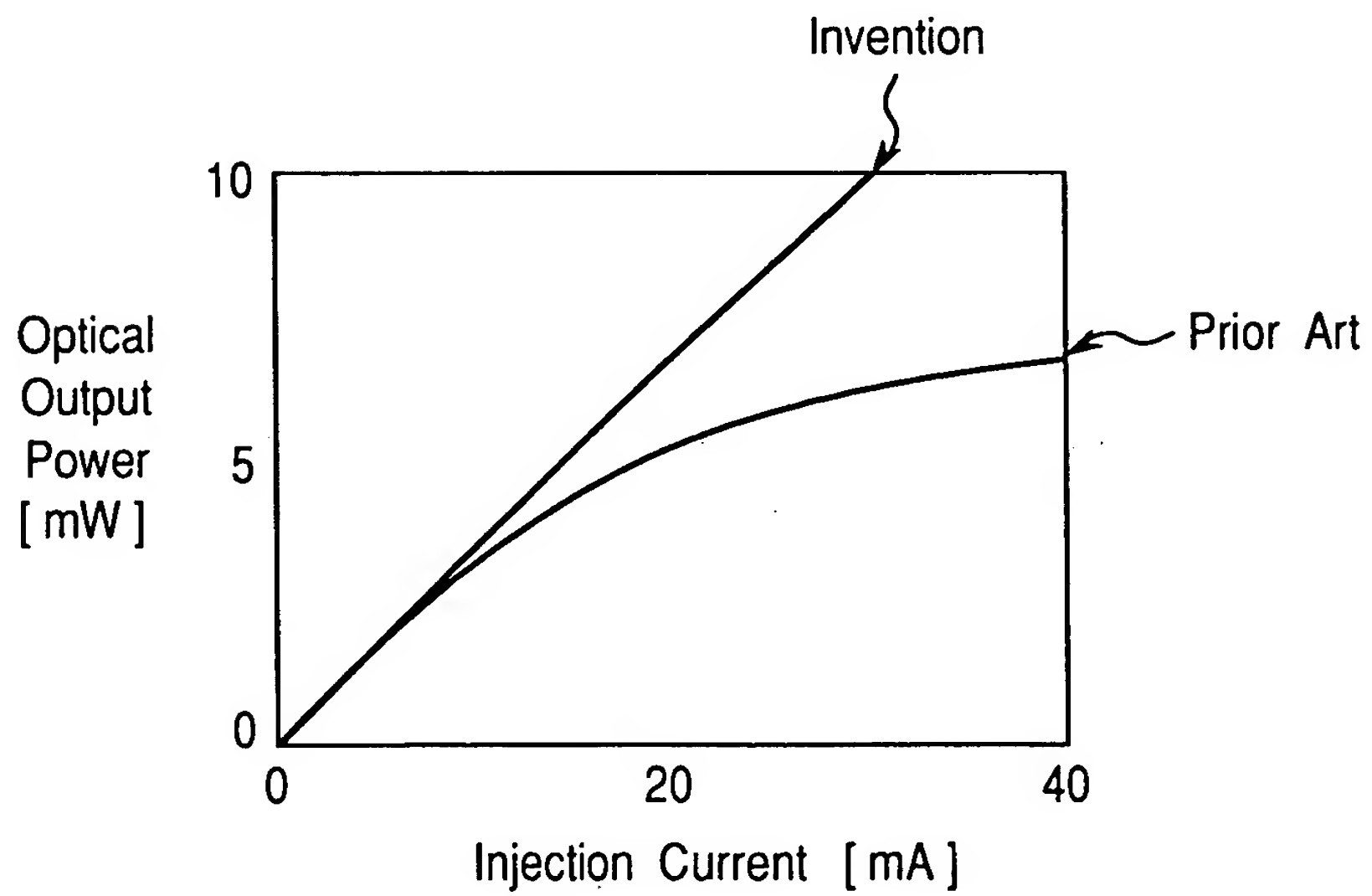


Fig.10

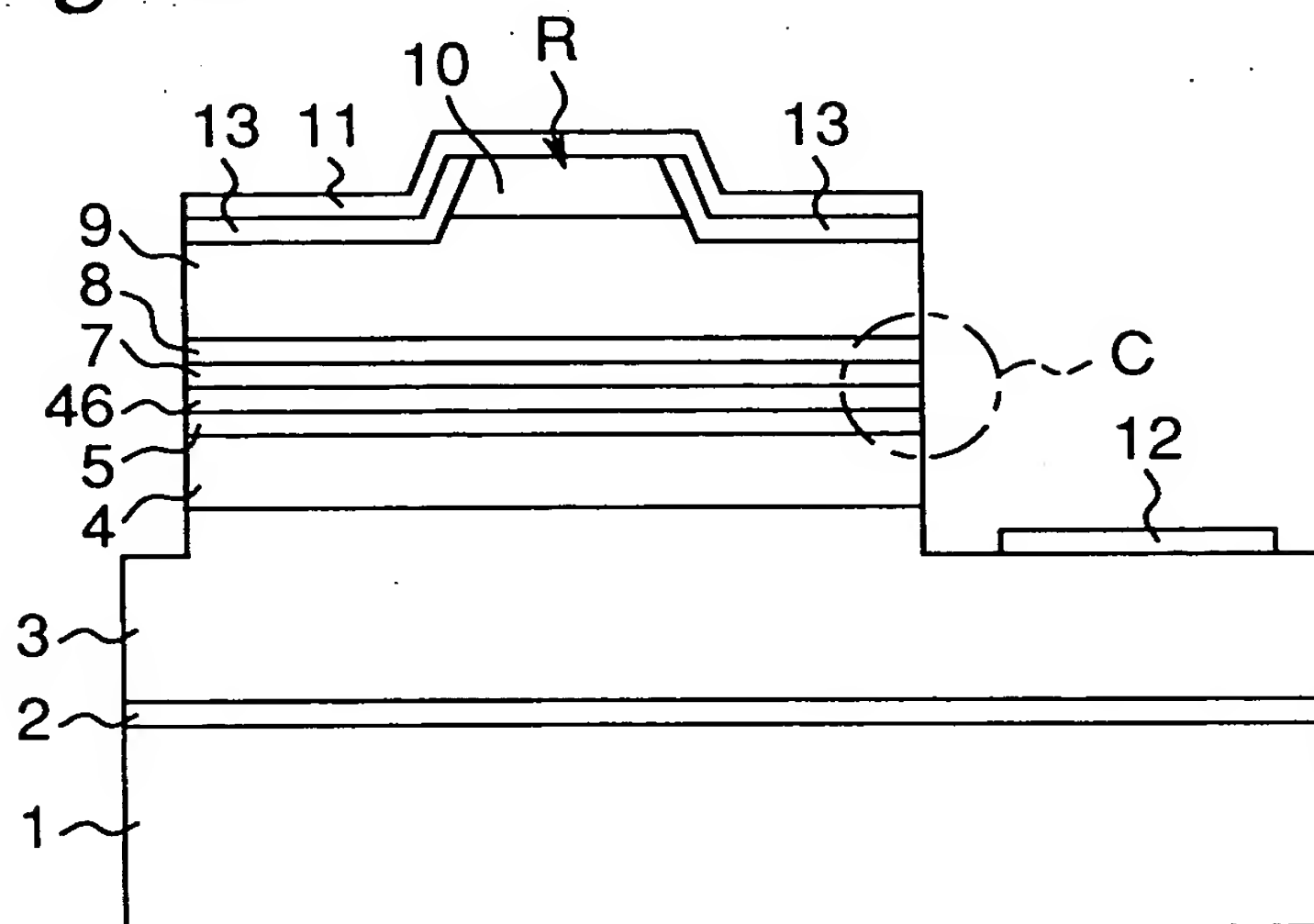


Fig.11

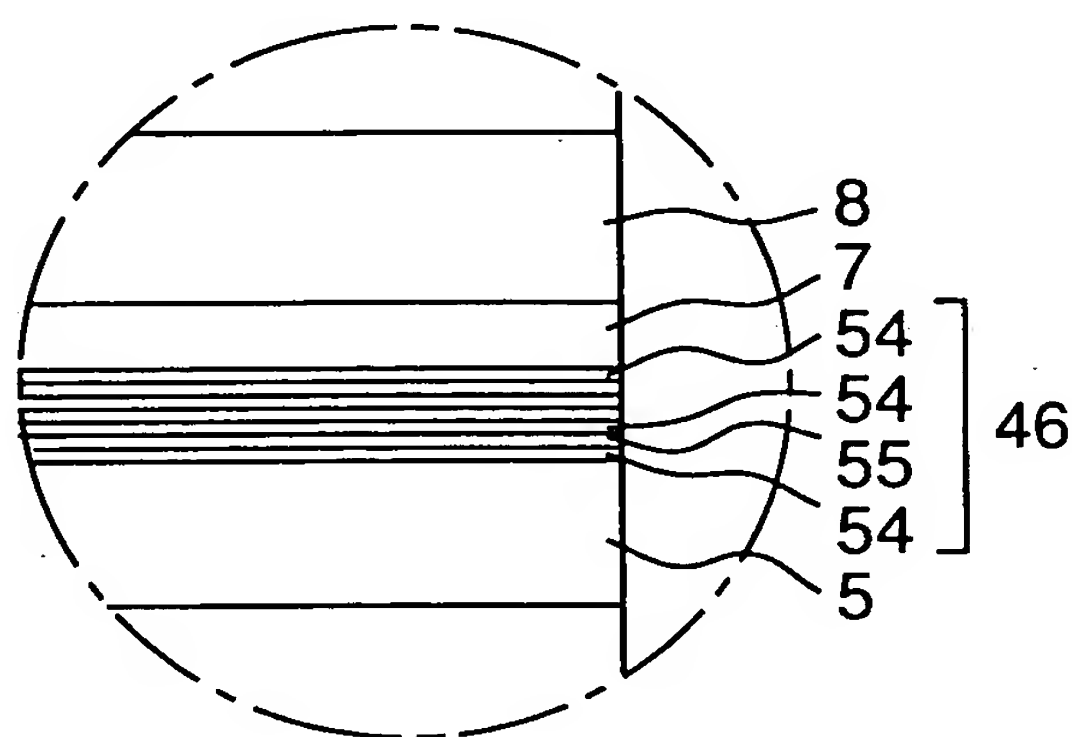


Fig.12

Frequency Capable of Modulating
 Optical Output power
 (Max. Frequency=●)

Threshold Current (○)

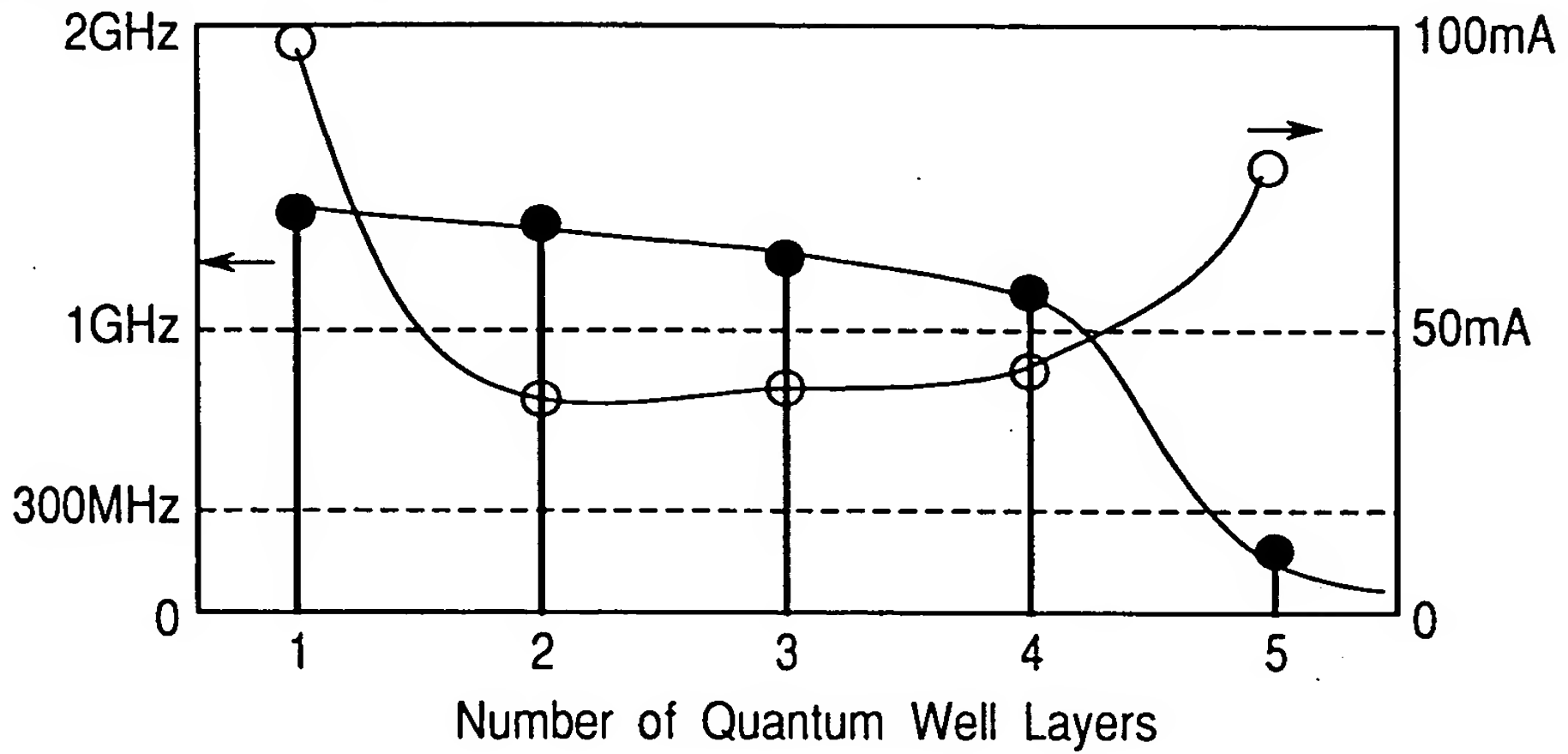


Fig.13

Frequency Capable of Modulating
 Optical Output power

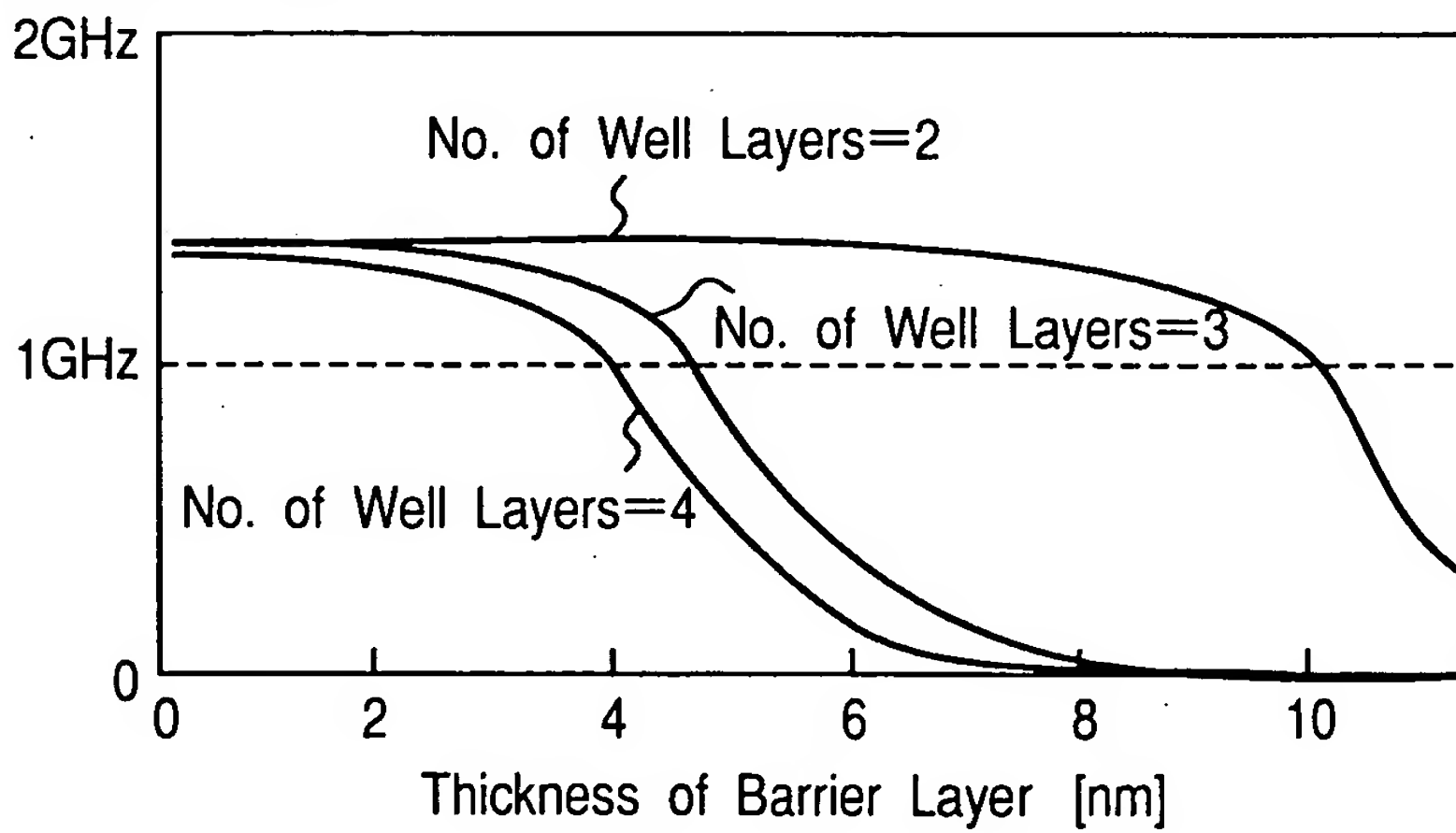


Fig.14

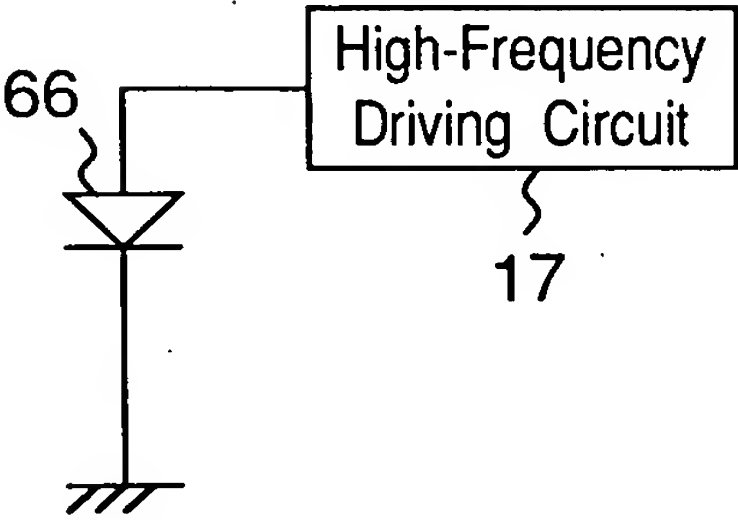


Fig.15

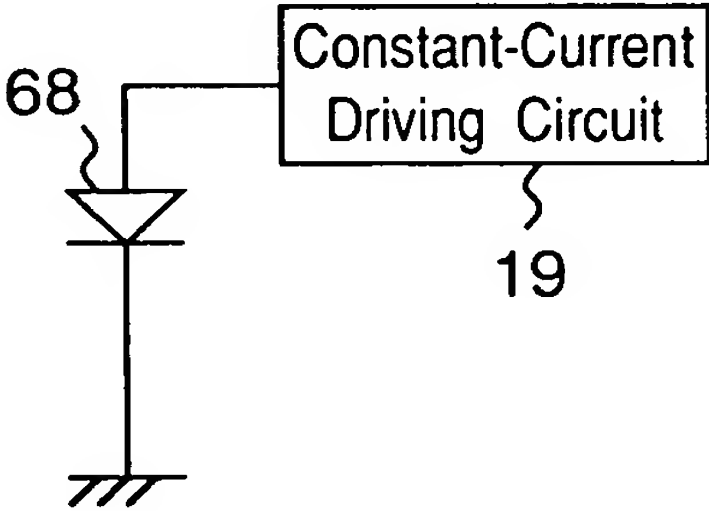


Fig.16

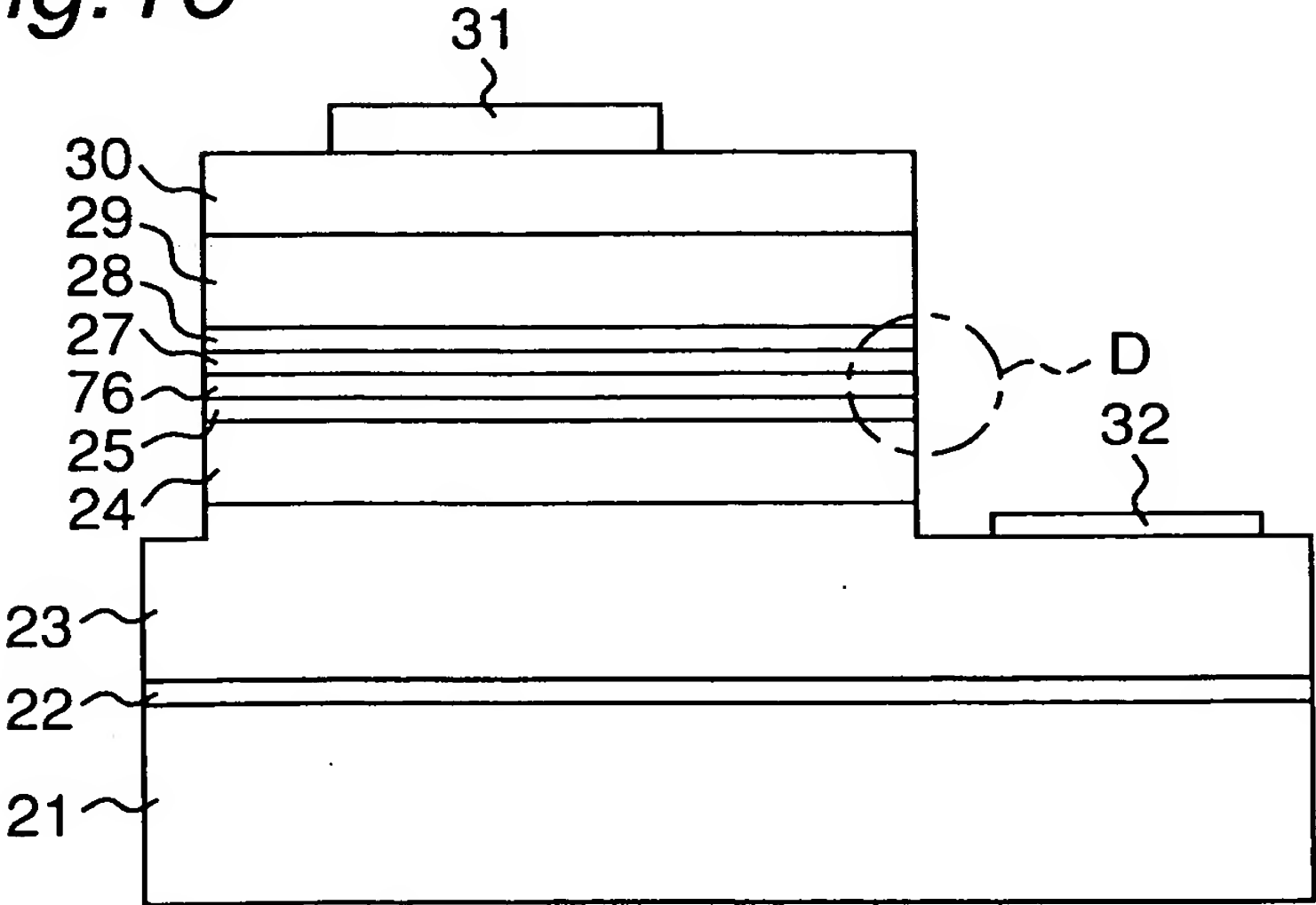


Fig.17

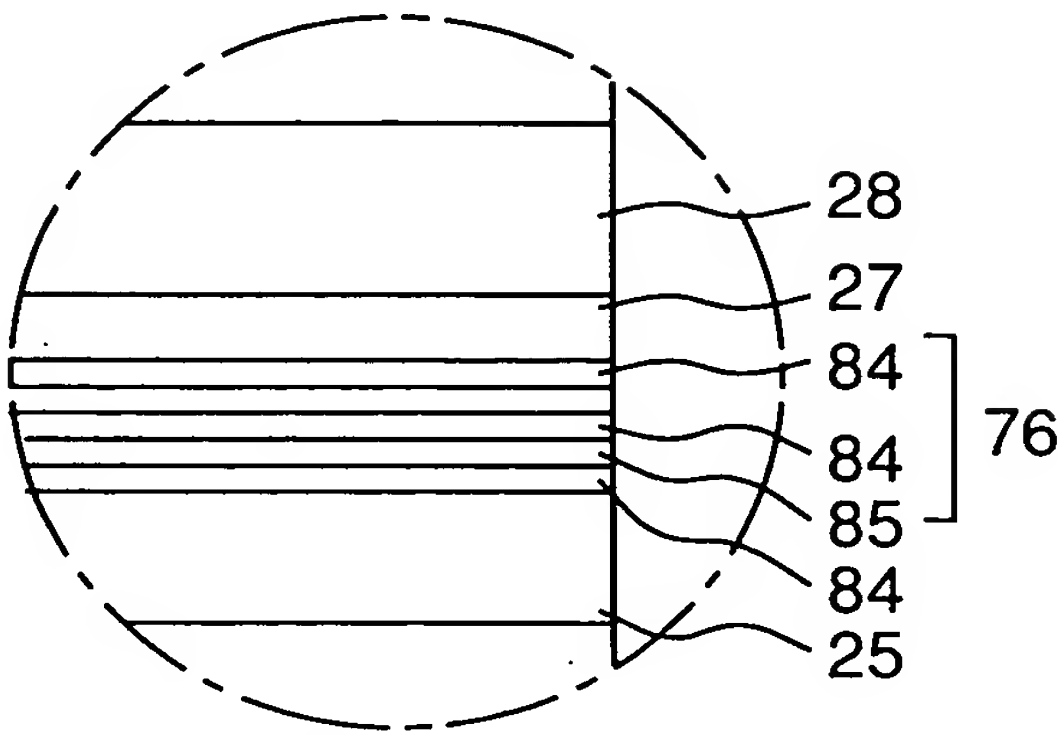


Fig.18

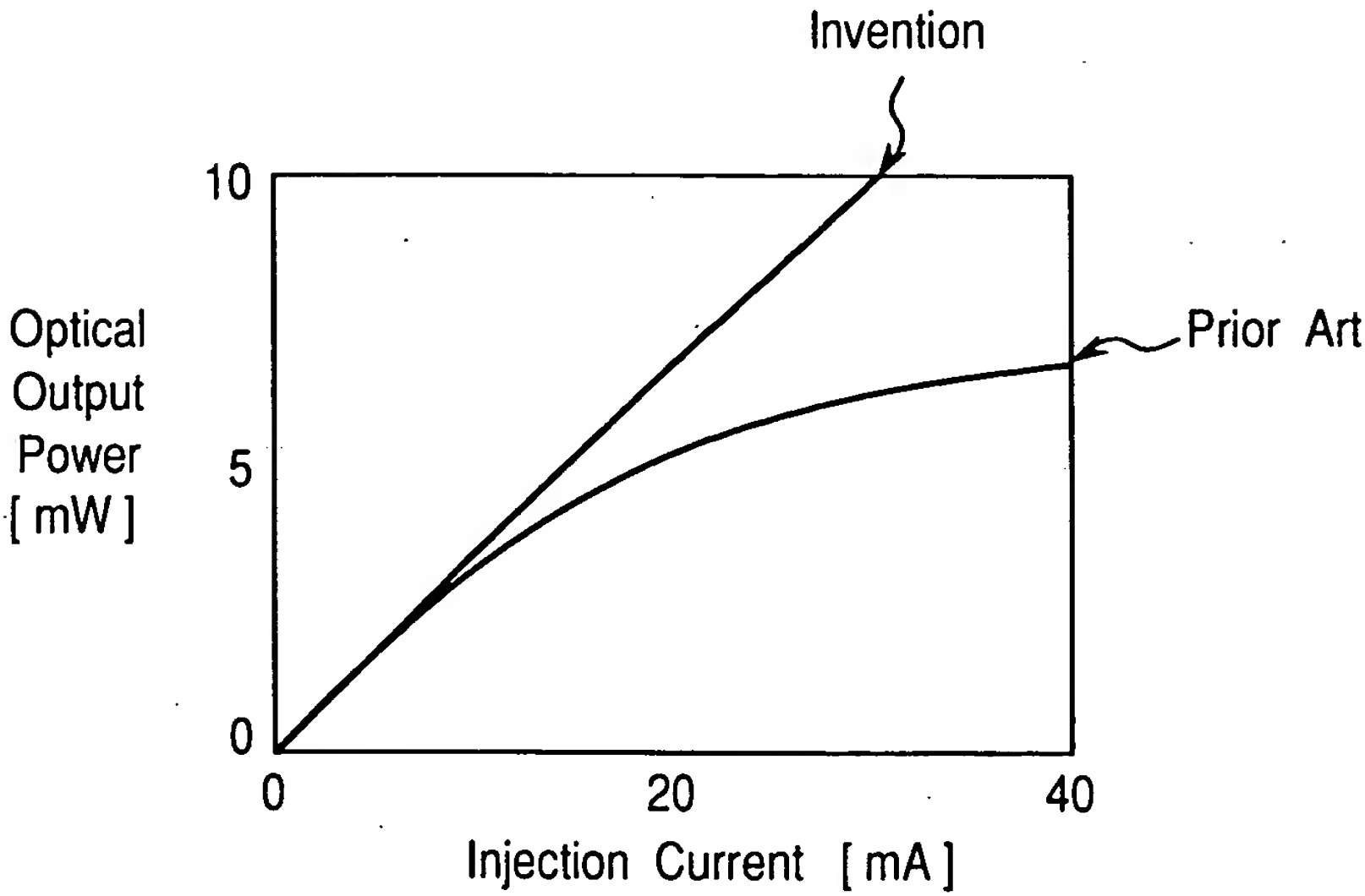


Fig.19

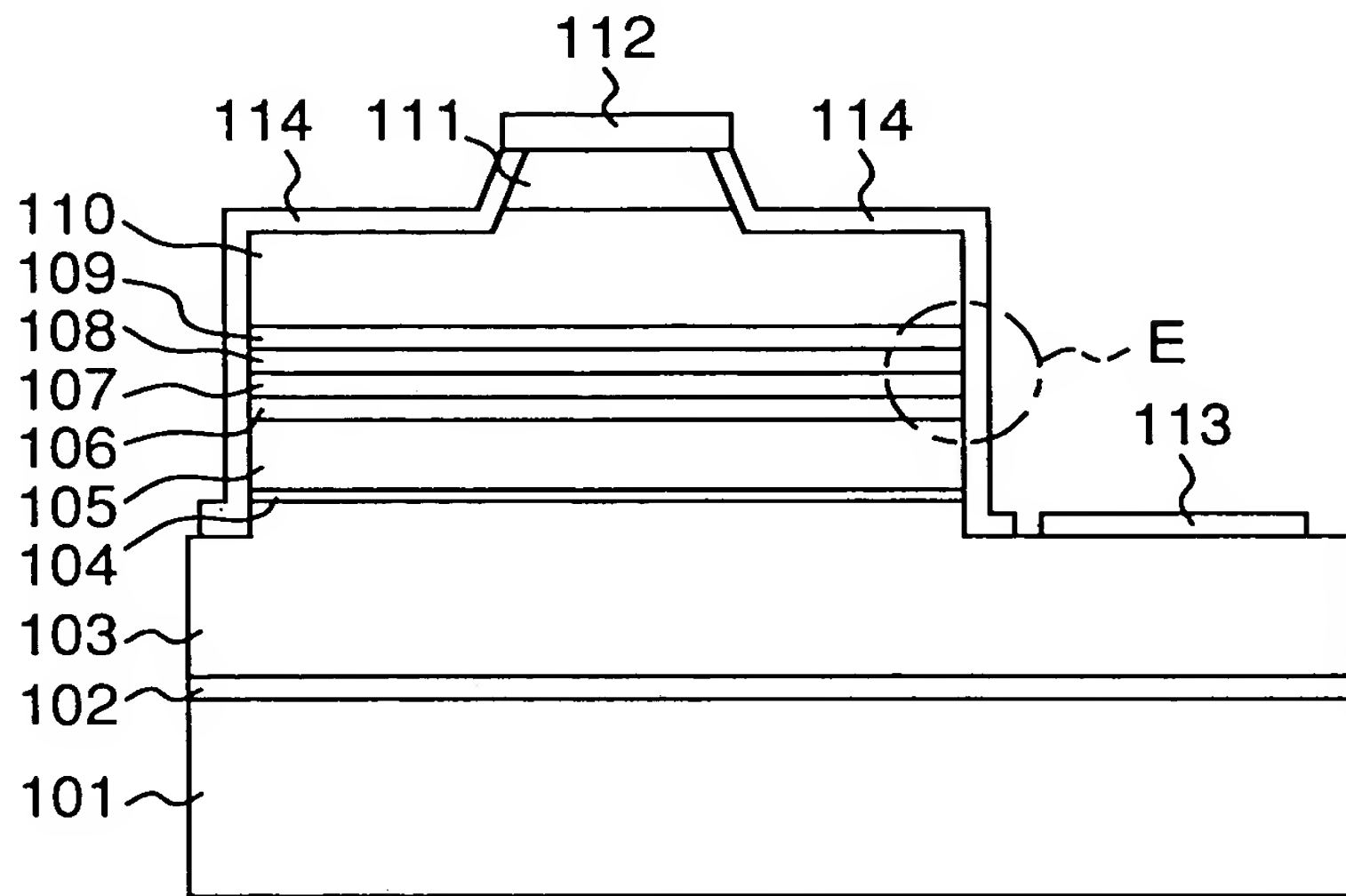
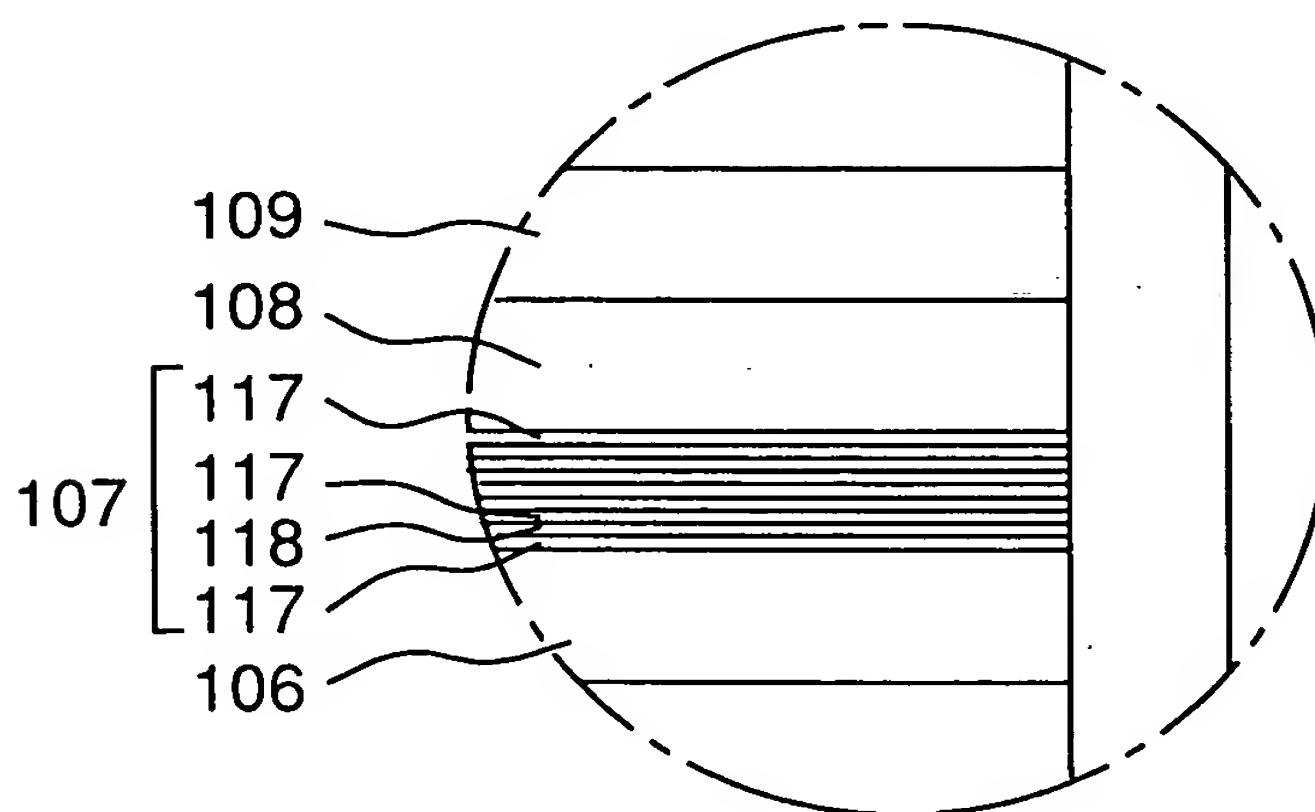


Fig.20



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Fig.21

